TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74AC573P,TC74AC573F,TC74AC573FT

Octal D-Type Latch with 3-State Output

The TC74AC573 is an advanced high speed CMOS OCTAL LATCH fabricated with silicon gate and double-layer metal wiring C^2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

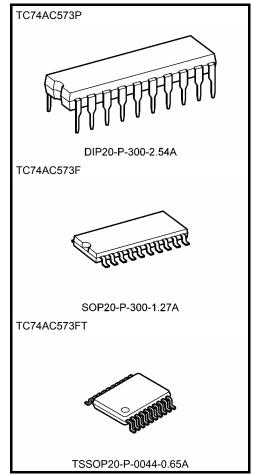
These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

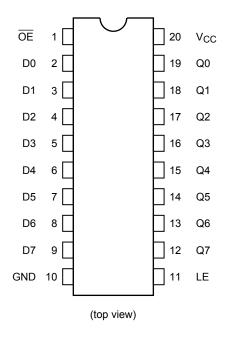
- High speed: $t_{pd} = 6.0 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 8 \mu A$ (max) at $T_a = 25$ °C
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Symmetrical output impedance: $|I_{OH}| = I_{OL} = 24$ mA (min) Capability of driving 50 Ω transmission lines.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2 to 5.5 V
- Pin and function compatible with 74F573



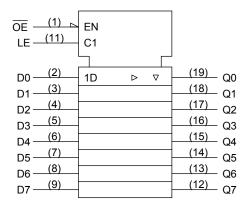
Weight

DIP20-P-300-2.54A : 1.30 g (typ.) SOP20-P-300-1.27A : 0.22 g (typ.) TSSOP20-P-0044-0.65A : 0.08 g (typ.)

Pin Assignment



IEC Logic Symbol



Truth Table

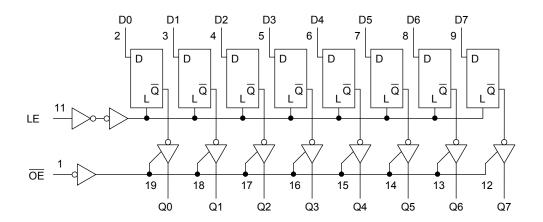
	Inputs	Output			
ŌĒ	LE	D	Q		
Н	Х	Х	Z		
L	L	Х	Q _n		
L	Н	L	L		
L	Н	Н	Н		

X: Don't care

Z: High impedance

 Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5 to 7.0	V
DC input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}	±20	mA
Output diode current	lok	±50	mA
DC output current	lout	±50	mA
DC V _{CC} /ground current	Icc	±200	mA
Power dissipation P _D		500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0 to 5.5	V
Input voltage	V _{IN}	0 to V _{CC}	٧
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	−40 to 85	°C
Input rise and fall time	dt/dV	0 to 100 (V _{CC} = 3.3 ± 0.3 V)	ns/V
input rise and rail tillle	ui/uv	0 to 20 (V _{CC} = 5 ± 0.5 V)	115/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

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Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40 to 85°C		Unit		
Characteristics	Cymbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Onit		
				2.0	1.50	_	_	1.50	_			
High-level input voltage	V_{IH}		_		3.0	2.10	_	_	2.10	_	V	
_					5.5	3.85	_	_	3.85	_		
					2.0	_	_	0.50	_	0.50		
Low-level input voltage	V_{IL}	_		3.0	_	_	0.90	_	0.90	V		
_					5.5	_	_	1.65	_	1.65		
					2.0	1.9	2.0	_	1.9	_		
			I _{OH} = -50 μA		3.0	2.9	3.0	_	2.9	_		
High-level output	V _{ОН}	V _{IN} = V _{IH} or V _{IL}			4.5	4.4	4.5	_	4.4	_	· V	
voltage			I _{OH} = -4 mA		3.0	2.58	_	_	2.48	_		
			I _{OH} = −24 mA		4.5	3.94	_	_	3.80	_		
			I _{OH} = -75 mA	(Note)	5.5	-	_	_	3.85	_		
	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA		2.0	_	0.0	0.1	_	0.1		
					3.0	_	0.0	0.1	_	0.1		
Low-level output					4.5	-	0.0	0.1	_	0.1	V	
voltage	VOL		I _{OL} = 12 mA		3.0	_	_	0.36	_	0.44		
			I _{OL} = 24 mA		4.5	_	_	0.36	_	0.44		
			I _{OL} = 75 mA	(Note)	5.5	-	_	_	_	1.65		
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	_	_	±0.5	_	±5.0	μΑ		
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		5.5	_	_	±0.1	_	±1.0	μΑ		
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND			5.5	_	_	8.0	_	80.0	μΑ	

Note: This spec indicates the capability of driving 50 Ω transmission lines.

One output should be tested at a time for a 10 ms maximum duration.

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition			Unit
			V _{CC} (V)	Limit	Limit	
Minimum pulse width	4		3.3 ± 0.3	7.0	7.0	20
(LE)	t _{w (H)}	_	5.0 ± 0.5	5.0	5.0	ns
Minimum set-up time	+		3.3 ± 0.3	7.0	7.0	20
Minimum set-up time	t _s	_	5.0 ± 0.5	4.0	4.0	ns
Minimum hold time	t _h		3.3 ± 0.3	1.0	1.0	20
		_	5.0 ± 0.5	1.0	1.0	ns



AC Characteristics (C_L = 50 pF, R_L = 500 Ω , input: t_r = t_f = 3 ns)

Characteristics	Symbol Test Condition			Ta = 25°C			Ta = -40 to 85°C		Unit
	.,		V _{CC} (V)	Min	Тур.	Max	Min	Max	
Propagation delay time	t _{pLH}	_	3.3 ± 0.3	_	9.4	15.4	1.0	17.6	ns
(LE-Q)	t _{pHL}		5.0 ± 0.5	_	6.6	9.9	1.0	11.3	
Propagation delay time	t _{pLH}	_	3.3 ± 0.3	_	9.4	16.0	1.0	18.2	ns
(Dn-Q)	t _{pHL}		5.0 ± 0.5	_	6.2	8.9	1.0	10.2	
Output enable time	t _{pZL}		3.3 ± 0.3	_	9.0	15.2	1.0	17.3	ns
Output enable time	t _{pZH}	_	5.0 ± 0.5	_	6.3	9.2	1.0	10.5	115
Output disable time	t _{pLZ}		3.3 ± 0.3	_	7.0	12.3	1.0	14.0	ns
Output disable time	t _{pHZ}	_	5.0 ± 0.5	_	6.0	8.8	1.0	10.0	113
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Output capacitance	C _{OUT}	_		_	10	_	_	_	pF
Power dissipation capacitance	C _{PD}		(Note)	_	32	-	-	_	pF

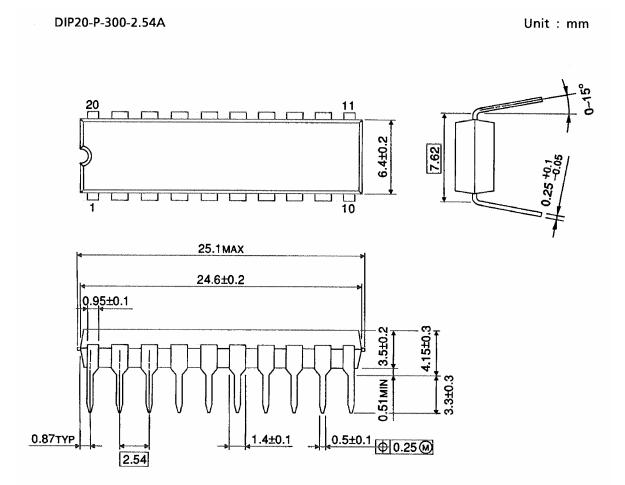
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per latch)$$

And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

Package Dimensions

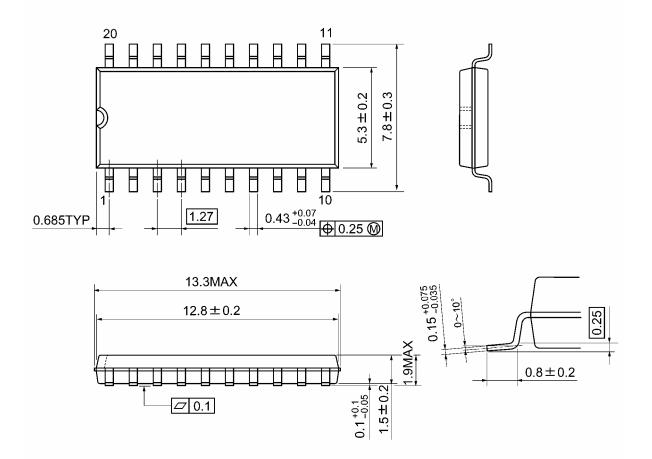


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Weight: 1.30 g (typ.)

Package Dimensions

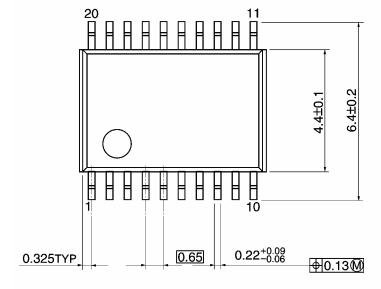
SOP20-P-300-1.27A Unit: mm

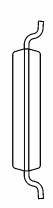


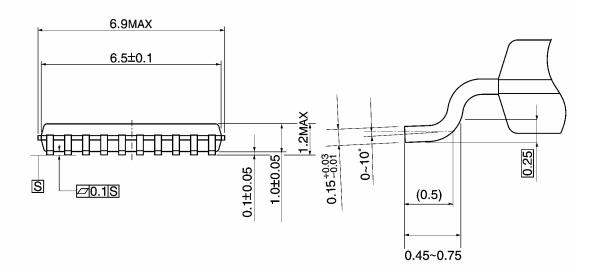
Weight: 0.22 g (typ.)

Package Dimensions

TSSOP20-P-0044-0.65A Unit: mm







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Weight: 0.08 g (typ.)

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20070701-EN GENERAL

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